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Journal of the European Ceramic Society 31 (2011) 2749-2752

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Short communication

Low temperature firing microwave dielectric ceramics $(K_{0.5}Ln_{0.5})MoO_4$ (Ln = Nd and Sm) with low dielectric loss

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Received 3 May 2011; received in revised form 5 July 2011; accepted 8 July 2011 Available online 17 August 2011

Abstract

In the present work, novel low temperature firing microwave dielectric ceramics ($K_{0.5}Ln_{0.5}$)MoO₄ (Ln = Nd and Sm) were prepared via the traditional solid state reaction method. A pure monoclinic phase can be formed at a low sintering temperature around 680 °C for both ($K_{0.5}Nd_{0.5}$)MoO₄ and ($K_{0.5}Sm_{0.5}$)MoO₄ ceramics. The densification temperature for the ($K_{0.5}Nd_{0.5}$)MoO₄ and ($K_{0.5}Sm_{0.5}$)MoO₄ ceramics are 700 °C and 800 °C for 2 h, respectively. The best microwave dielectric properties for ($K_{0.5}Nd_{0.5}$)MoO₄ was obtained in ceramic sample sintered at 760 °C for 2 h, with a dielectric permittivity of 9.8, a Qf about 69,000 GHz and a temperature coefficient of frequency about -62 ppm/°C. The best microwave dielectric properties for ($K_{0.5}Sm_{0.5}$)MoO₄ was obtained in ceramic sample sintered at 800 °C for 2 h, with a dielectric permittivity of 9.7, a Qf about 20,000 GHz and a temperature coefficient of frequency about -65 ppm/°C. © 2011 Elsevier Ltd. All rights reserved.

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Keywords: Sintering; Dielectric properties

1. Introduction

With the development of wireless communication and satellite broadcasting industry, the multilayer co-fired ceramics (MLCC) and low-temperature co-fired ceramics technology (LTCC) have played an important role in the fabrication process to meet the requirement of miniaturization and integration. The LTCC technology requires the microwave dielectric ceramics to have lower sintering temperatures than that of the inner electrode materials. In addition to the common method of adding sintering aids, such as low melting point oxides and low softening glasses, the employment of materials with intrinsic low sintering temperatures (so called low firing ceramics) is also an efficient way and has attracted much attention in recent years.^{1–4}

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0955-2219/\$ – see front matter © 2011 Elsevier Ltd. All rights reserved. doi:10.1016/j.jeurceramsoc.2011.07.009

In the past more than ten years, most of the low firing ceramics are TeO₂-rich compounds, such as BaO-TeO₂ system,^{5,6} MgO-TeO₂ system,⁷ ZnO-TeO₂ system,⁸ CaO-TeO₂ system,⁹ Bi₂O₃-TeO₂ system,¹⁰ and (Zr,Ti,Sn)O₂-TeO₂ system.^{11,12} In the recent few years, the research on the low firing ceramics was not only limited in the TeO₂-rich systems but expanded to the universal oxide systems with low melting points, such as Bi₂O₃-rich compounds, V₂O₅-rich compounds, MoO₃-rich compounds, P₂O₅-rich compounds, B₂O₃-rich compounds.¹³⁻²⁰ Among them, many MoO₃-rich low firing ceramics show high microwave dielectric performance and some of them can be co-fired with aluminum.^{4,15,20} In this work, novel MoO_3 -rich (K_{0.5}Ln_{0.5})MoO₄ (Ln = Nd and Sm) compounds were prepared via the solid state reaction method. The phase evolution, microstructure, and microwave dielectric properties were investigated.

2. Experimental

Proportionate amounts of reagent-grade starting materials of K₂CO₃, Nd₂O₃, Sm₂O₃ (>99%, Guo-Yao Co, Ltd, Shanghai,

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Fig. 1. X-ray diffraction patterns of the $(K_{0.5}Ln_{0.5})MoO_4$ (Ln = Nd and Sm) ceramics calcined and sintered at different temperatures.

China) and MoO₃ (>99%, Fuchen Chemical Reagents, Tianjin, China) were weighed according to the stoichiometric formulation ($K_{0.5}Ln_{0.5}$)MoO₄ (Ln = Nd and Sm) compositions. Powders were mixed and milled for 4 h using a planetary mill (Nanjing Machine Factory, Nanjing, China) by setting the running speed at 150 rpm with the Yttria Stabilized Zirconia (2 mm in diameter) milling media. The mixed oxides were then calcined at 600 °C for 4 h. After being crushed and re-milled for 5 h using the ZrO₂ milling media and deionized water, powders were pressed into cylinders (10 mm in diameter and 5 mm in height) in a steel die with 5 wt.% PVA binder addition under a uniaxial pressure of 200 MPa. Samples were sintered in the temperature range from 640 °C to 860 °C for 2 h.

The crystalline structures of samples were investigated using X-ray diffraction with Cu K α radiation (Rigaku D/MAX-2400 X-ray diffractometer, Tokyo, Japan). Microstructures of sintered ceramic were observed on the as-fired surface and fractured surfaces with scanning electron microscopy (SEM) (JSM-6460, JEOL, Tokyo, Japan). Dielectric behaviors at microwave frequency were measured with the TE_{01δ} shielded cavity method with a network analyzer (8720ES, Agilent, Palo Alto, CA) and a temperature chamber (Delta 9023, Delta Design, Poway, CA). The temperature coefficient of resonant frequency τ_f (TCF) was calculated with the following formula:

$$\tau_f = \frac{f_{85} - f_{25}}{f_{25} \times (85 - 25)} \times 10^6 \tag{1}$$

where f_{85} and f_{25} were the TE_{01 δ} resonant frequencies at 85 °C and 25 °C, respectively.

3. Results and discussion

Fig. 1 shows the X-ray diffraction patterns of the $(K_{0.5}Ln_{0.5})MoO_4$ (Ln = Nd and Sm) ceramics calcined and sintered at different temperatures. It was reported that there exist many different modifications of the structure for $(K_{0.5}Ln_{0.5})MoO_4$ compounds (Ln = rare earth element), depending on the size and nature of the rare earth element and the compound formation conditions.^{21–23} In general, these compounds can be divided into two groups: (1) scheelite-type modifications including phases with an $(K_{0.5}Eu_{0.5})MoO_4$ -type structure (space group $P\overline{1}$) and (2) non-scheelite modifications with the $(K_{0.5}Y_{0.5})MoO_4$ -type structure (space group *Pbcn*).²⁴ Comparing our experimental data with the literatures', it is found that both the $(K_{0.5}Nd_{0.5})MoO_4$ and $(K_{0.5}Sm_{0.5})MoO_4$ prepared via the solid state reaction method here have the same structure with $(K_{0.5}Eu_{0.5})MoO_4$ (PDF: 31-1006).²⁵ Using a $Ag_{1/8}Pr_{5/8}MoO_4^{26}$ structure as the starting model, Morozov et al.²⁴ found that both the $(K_{0.5}Nd_{0.5})MoO_4$ and $(K_{0.5}Eu_{0.5})MoO_4$ could be well indexed in the same monoclinic superspace group, $I2/b(\alpha \beta 0)00$. The XRD patterns of $(K_{0.5}Nd_{0.5})MoO_4$ as shown in Fig. 1(a) was also indexed as this superspace group. Similarly, the detailed crystal structure report on the (K_{0.5}Sm_{0.5})MoO₄ has been done by Arakcheeva



Fig. 2. SEM photos of the (K_{0.5}Nd_{0.5})MoO₄ ceramic sintered at 760 °C for 2 h and (K_{0.5}Sm_{0.5})MoO₄ ceramic sintered at 800 °C for 2 h.



Fig. 3. Microwave dielectric permittivity and Qf values of the $(K_{0.5}Ln_{0.5})MoO_4$ (Ln = Nd and Sm) ceramics as a function of sintering temperature.

et al.²⁷ and it also can be indexed as the monoclinic superspace group, $I2/b(\alpha \beta 0)00$. From Fig. 1(b), our experimental results agree well with the literatures'. Furthermore, this monoclinic scheelite-related phase can be formed at a low temperature 680 °C for both (K_{0.5}Nd_{0.5})MoO₄ and (K_{0.5}Sm_{0.5})MoO₄ prepared via the simple solid state reaction method.

The SEM photos of the ($K_{0.5}Nd_{0.5}$)MoO₄ ceramic sintered at 760 °C for 2 hrs and ($K_{0.5}Sm_{0.5}$)MoO₄ ceramic sintered at 800 °C for 2 h are shown in Fig. 2. Both homogenous and dense microstructure can be observed. It is seen that the grain size of ($K_{0.5}Nd_{0.5}$)MoO₄ ceramic sintered at 760 °C for 2 h lies between 1 and 3 µm, which is much smaller than 3–7 µm for ($K_{0.5}Sm_{0.5}$)MoO₄ ceramic sintered at 800 °C/2 h. In fact, from the density results (the figure is not presented here), the ($K_{0.5}Nd_{0.5}$)MoO₄ ceramic can be well densified when the sintering temperature is above 700 °C while the densification temperature of ($K_{0.5}Sm_{0.5}$)MoO₄ ceramic is 800 °C. The SEM photos also confirm this result.

Microwave dielectric permittivity and Qf value of the $(K_{0.5}Ln_{0.5})MoO_4$ (Ln = Nd and Sm) ceramics as a function of sintering temperature are shown in Fig. 3. The microwave dielectric permittivity of (K_{0.5}Nd_{0.5})MoO₄ ceramic first increased sharply from 7.6 at a sintering temperature of 640 °C to about 9.8 for the ceramic sample sintered at 680 °C along with the elimination of pores during the sintering process. It kept stable in the sintering temperature range 680–760 °C and then decreased slightly, which might be caused by the secondary grain growth, potassium volatilization, etc. The microwave dielectric permittivity of (K_{0.5}Sm_{0.5})MoO₄ ceramic has the similar trend but its densification temperature is around 800 °C. The Qf value of microwave dielectric ceramics is influenced by many factors during the sintering process, such as the grain size, grain size distribution, pores, etc. Although the intrinsic part can be extrapolated from the infrared spectra data, the real Qf value including both intrinsic and extrinsic parts can only be analyzed qualitatively. The largest Qf value about 69,000 GHz of (K_{0.5}Nd_{0.5})MoO₄ ceramic was obtained in ceramic sample sintered at 760 °C for 2 h. It is very sensitive to the sintering temperature, and large Qf values can only be obtained in a very narrow sintering temperature range. The Qf value of (K_{0.5}Sm_{0.5})MoO₄ ceramic was about 20,000 GHz when



Fig. 4. Microwave dielectric permittivity and Qf values of the $(K_{0.5}Ln_{0.5})MoO_4$ (Ln = Nd and Sm) ceramics as a function of temperature.

above 800 °C, which was smaller than that of $(K_{0.5}Nd_{0.5})MoO_4$ ceramic, but it seems much more stable against the sintering temperature.

To further understand the temperature dependence of the microwave dielectric properties of $(K_{0.5}Ln_{0.5})MoO_4$ (Ln = Nd and Sm) ceramics, the microwave dielectric permittivity and Qf value measured in the temperature range 25–120 °C are demonstrated in Fig. 4. It can be seen that the microwave dielectric permittivity of both $(K_{0.5}Nd_{0.5})MoO_4$ and $(K_{0.5}Sm_{0.5})MoO_4$ ceramics linearly increased with the temperature slightly without any abnormity. The Qf value of $(K_{0.5}Nd_{0.5})MoO_4$ ceramic decreased slightly from 69,000 GHz at 20 °C to 64,000 GHz at 120 °C. The Qf value of $(K_{0.5}Sm_{0.5})MoO_4$ ceramic increased slightly from 20,000 GHz at 20 °C to 31,000 GHz at 120 °C. The temperature coefficient for $(K_{0.5}Nd_{0.5})MoO_4$ and $(K_{0.5}Sm_{0.5})MoO_4$ ceramics are -62 ppm/°C and -65 ppm/°C, respectively.

4. Conclusion

The monoclinic ($K_{0.5}Nd_{0.5}$)MoO₄ and ($K_{0.5}Sm_{0.5}$)MoO₄ ceramics were prepared via the solid state reaction method. The best microwave dielectric properties for ($K_{0.5}Nd_{0.5}$)MoO₄ was obtained in ceramic sample sintered at 760 °C for 2 h, with a dielectric permittivity of 9.8, a Qf about 69,000 GHz and a temperature coefficient of frequency about -62 ppm/°C. The best microwave dielectric properties for ($K_{0.5}Sm_{0.5}$)MoO₄ was obtained in ceramic sample sintered at 800 °C for 2 h, with a dielectric permittivity of 9.7, a Qf about 20,000 GHz and a temperature coefficient of frequency about -65 ppm/°C.

Acknowledgements

This work was supported by National Science Foundation of China (61025002, 10979035), National 973-project of China (2009CB623302) and International Science and Technology Collaboration Project of China (2009DFA51820).

References

 Sebastian MT, Jantunen H. Low loss dielectric materials for LTCC applications: a review. Int Mater Rev 2008;53:57–90.

- Axelsson AK, Alford NM. Bismuth titanates candidates for high permittivity LTCC. J Eur Ceram Soc 2006;26:1933–6.
- Shlyakhtin OA, Oh YJ. Low temperature sintering of Zn₃Nb₂O₈ C ceramics from fine powders. J Am Ceram Soc 2006;89:3366–72.
- Zhou D, Wang H, Pang LX, Randall CA, Yao X. Bi₂O₃-MoO₃ binary system: an alternative ultra low sintering temperature microwave dielectric. *J Am Ceram Soc* 2009;92:2242–6.
- Kwon DK, Lanagan MT, Shrout TR. Microwave dielectric properties of BaO–TeO₂ binary compounds. *Mater Lett* 2007;61:1827–31.
- Kwon DK, Lanagan MT, Shrout TR. Microwave dielectric properties and low-temperature cofiring of BaTe₄O₉ with aluminum metal electrode. J Am Ceram Soc 2005;88:3419–22.
- Subodh G, Ratheesh R, Jacob MV, Sebastian MT. Microwave dielectric properties and bibrational spectroscopic analysis of MgTe₂O₅ ceramics. J Mater Res 2008;23:1551–6.
- Subodh G, Sebastian MT. Glass-free Zn₂Te₃O₈ microwave ceramic for LTCC applications. *J Am Ceram Soc* 2007;90:2266–8.
- Valant M, Suvorov D. Glass-free low-temperature cofired ceramics: calcium germanates, silicates and tellurates. *J Eur Ceram Soc* 2004;24:1715–9.
- Udovic M, Valant M, Suvorov D. Phase formation and dielectric characterization of the Bi₂O₃-TeO₂ system prepared in an oxygen atmosphere. J Am Ceram Soc 2004;87:591–7.
- Udovic M, Valant M, Suvorov D. Dielectric characterisation of ceramics from the TiO₂-TeO₂ system. *J Eur Ceram Soc* 2001;21: 1735–8.
- 12. Subodh G, Sebastian MT. Microwave dielectric properties of ATe_3O_8 (A = Sn Zr) ceramics. *J Appl Phys* 2008;**47**:7943–6.
- Valant M, Suvorov D. Chemical compatibility between silver electrodes and low-firing binary-oxide compounds: conceptual study. J Am Ceram Soc 2000;83:2721–9.
- Feteira A, Sinclair DC. Microwave dielectric properties of low firing temperature Bi₂W₂O₉ ceramics. J Am Ceram Soc 2008;91:1338–41.
- Zhou D, Wang H, Yao X, Pang LX. Microwave dielectric properties of low temperature firing Bi₂Mo₂O₉ ceramic. J Am Ceram Soc 2008;91:3419–22.

- Umemura R, Ogawa H, Ohsato H, Kan A, Yokoi A. Microwave dielectric properties of low-temperature sintered Mg₃(VO₄)₂ ceramic. *J Eur Ceram Soc* 2005;25:2865–70.
- Choi GK, Kim JR, Yoon SH, Hong KS. Microwave dielectric properties of scheelite (A = Ca, Sr, Ba) and wolframite (A = Mg, Zn Mn) AMoO₄ Compounds. *J Eur Ceram Soc* 2007;**27**:3063–7.
- Bian JJ, Kim DW, Hong KS. Microwave dielectric properties of A₂P₂O₇ (A = Ca, Sr, Ba; Mg, Zn Mn). Jpn J Appl Phys 2004;43:3521–5.
- Takada T, Kageyama K. Synthesis and microwave dielectric properties of La₂O₃-xB₂O₃-based melt mixtures for low-temperature cofired ceramics. *Jpn J Appl Phys* 2005;44:6629–35.
- Zhou D, Randall CA, Wang H, Pang LX, Yao X. Microwave dielectric ceramics in Li₂O–Bi₂O₃–MoO₃ system with ultra-low sintering temperatures. *J Am Ceram Soc* 2010;**93**:1096–100.
- Klevtsov PV, Klevtsova RF. Polymorphism of double molybdates and tungstates of mono-valent and trivalent metals with composition M⁺R³⁺(EO₄)₂. J Struct Chem 1977;18:339–55.
- Sokolovskii BM, Evdokimov AA, Trunov VK. Double molybdates of potassium and rare-earth elements. *Zh Neorg Khim* 1977;22:1499–504.
- Klevtsov PV, Kozeeva LP. Crystal modificatios of double potassium molybdates with samarium, europium and gadolinium, KLn(MoO₄)₂. *Kristallografiya* 1976;21:316–21.
- Morozov VA, Arakcheeva AV, Chapuis G, Guiblin N, Rossell MD, Van Tendeloo G. KNd(MoO₄)₂: a new incommensurate modulated structure in the scheelite family. *Chem Mater* 2006;**18**:4075–82.
- Rybakov VK, Trunov VK. Double molybdates of heavy alkaline and rare earth elements. *Zh Neorg Khim* 1971;16:1320–5.
- Morozov VA, Mironov AV, Lazoryak BI, Khaikina EG, Basovich OM, Rossell MD, Van Tendeloo G. Ag_{1/8}Pr_{5/8}MoO₄: an incommensurately modulated scheelite-type structure. *J Solid State Chem* 2006;**179**:1183– 91.
- Arakcheeva A, Pattison P, Chapuis G, Rossell M, Filaretov A, Morozov V, Tendeloo GV. KSm(MoO₄)₂, an incommensurately modulated and partially disordered scheelite-like structure. *ACTA Crystallogr B* 2008;64:160–71.